

IN THE CLAIMS:

The text of all pending claims, (including withdrawn claims) is set forth below. Cancelled and not entered claims are indicated with claim number and status only. The claims as listed below show added text with underlining and deleted text with ~~strikethrough~~. The status of each claim is indicated with one of (original), (currently amended), (cancelled), (withdrawn), (new), (previously presented), or (not entered).

Please AMEND claims 1, 6, 7 and 12 in accordance with the following:

1. **(Currently Amended)** A thin film transistor (TFT) comprising:
 a channel region having a plurality of crystal grain boundaries;
 source and drain regions respectively formed at opposite ends of the channel region; and
 an offset regions formed between the source and drain regions and the channel region,
 ~~having no doping and a plurality of primary crystal grain boundaries,~~ wherein the thin film transistor is formed so that the primary crystal grain boundaries of a polysilicon substrate are not positioned in the offset regions, and wherein a width of each one of the offset regions, ~~included in an activation layer,~~ is smaller than a distance between the primary crystal grain boundaries formed in the channel region.
2. **(Cancelled)**
3. **(Original)** The thin film transistor according to claim 1, wherein the polysilicon substrate is formed by a sequential lateral solidification (SLS) method.
4. **(Original)** The thin film transistor according to claim 1, wherein the thin film transistor is used in an LCD (liquid crystal display) or organic EL (electroluminescent) device.
5. **(Previously Presented)** The thin film transistor according to claim 1, wherein the primary crystal grain boundaries are substantially perpendicular to a current direction between the source and drain regions of the thin film transistor.

6. **(Currently Amended)** A thin film transistor (TFT) comprising:
a channel region;
source and drain regions respectively formed at opposite sides of the channel region;
a lightly doped drain (LDD) region or offset region respectively formed at opposite sides
of the channel region and between the source and drain regions; and
a plurality of primary crystal grain boundaries, wherein the thin film transistor is formed so
that the primary crystal grain boundaries of a polysilicon substrate are positioned in the channel,
source and drain regions but not positioned in the LDD or offset region, and wherein a width of
the LDD region or offset regions is less than a distance between two adjoining primary crystal
grain boundaries.
7. **(Currently Amended)** A flat panel display device comprising:
a thin film transistor comprising:
a channel region;
an offset regions formed at opposite sides of the channel region, the offset
regions having no doping;
source and drain regions respectively formed at outer sides of the offset regions;
and
a plurality of primary crystal grain boundaries,
wherein the thin film transistor is formed so that the primary crystal grain boundaries of a
polysilicon substrate are not positioned in the offset regions, and wherein a width of the offset
regions, ~~included in an activation layer,~~ is smaller than a distance between the primary crystal
grain boundaries.
8. **(Cancelled)**
9. **(Original)** The flat panel display device according to claim 7, wherein the
polysilicon substrate is formed by a sequential lateral solidification (SLS) method.
10. **(Original)** The flat panel display device according to claim 7, wherein the thin
film transistor is used in an LCD (liquid crystal display) or organic EL (electroluminescent)
device.

11. **(Previously Presented)** The flat panel display device according to claim 7, wherein the primary crystal grain boundaries are substantially perpendicular to a current direction between the source and drain regions of the thin film transistor.

12. **(Currently Amended)** A flat panel display device comprising:
a thin film transistor comprising:
a ~~lightly~~lightly doped drain (LDD) region or offset region, and a plurality of primary crystal grain boundaries,
wherein the thin film transistor is formed so that the primary crystal grain boundaries of a polysilicon substrate are positioned in channel, source and drain regions but not positioned in the LDD or offset region, and
wherein a width of the LDD region or offset region is less than a distance between two adjoining primary crystal grain boundaries.

13 - 14. **(Cancelled)**